# MSKSEMI 美森科













ESD

/S

TSS

MOV

GDT

PIFD

# **MMST3904**

Product specification

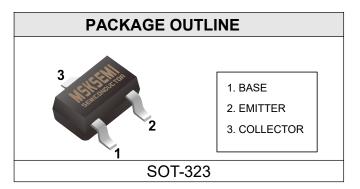




#### **FEATURES**

Complementary to MMST3906

#### **Reference News**



## MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)

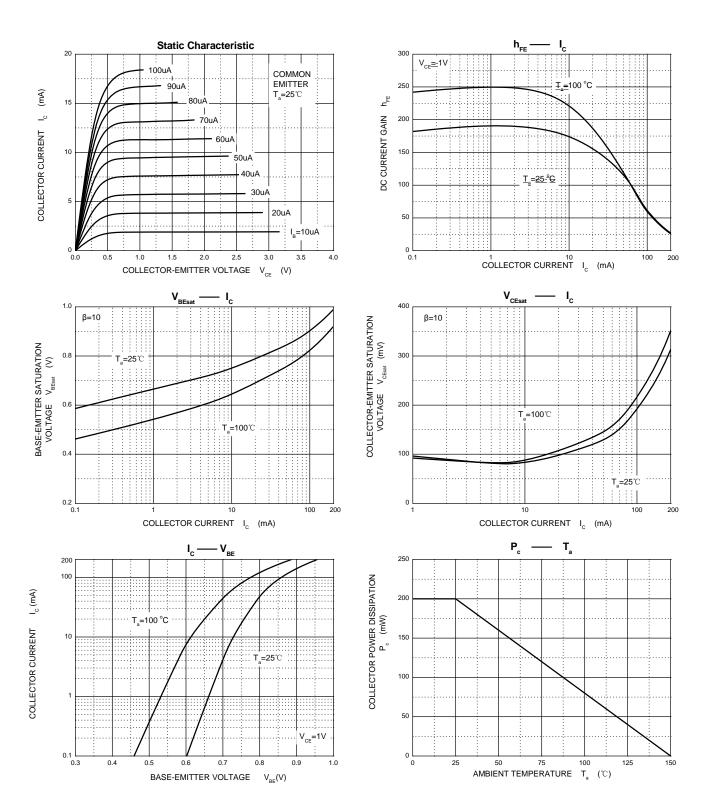
Symbol	Parameter	Value	Unit
V <sub>СВО</sub>	Collector-Base Voltage	60	V
Vceo	Collector-Emitter Voltage	40	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
lc	Collector Current	200	mA
Pc	Collector Power Dissipation	200	mW
Roja	Thermal Resistance From Junction To Ambient	625	°C/W
T <sub>J</sub> ,T <sub>stg</sub>	Operation Junction and Storage Temperature Range	-55 ~ +150	°C

## **ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub> *	I <sub>C</sub> =10μA, I <sub>E</sub> =0	60			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub> *	I <sub>C</sub> =1mA, I <sub>B</sub> =0	40			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub> *	I <sub>E</sub> =10μA, I <sub>C</sub> =0	5			V
Collector cut-off current	I <sub>CBO</sub> *	V <sub>CB</sub> =60V, I <sub>E</sub> =0			60	nA
Collector cut-off current	ICEX	V <sub>CE</sub> =30V, V <sub>BE(off)</sub> =3V			50	nA
	h <sub>FE</sub> *	V <sub>CE</sub> =1V, I <sub>C</sub> =100μA	40			
		V <sub>CE</sub> =1V, I <sub>C</sub> =1mA	70			
DC current gain		V <sub>CE</sub> =1V, I <sub>C</sub> =10mA	100		300	
		V <sub>CE</sub> =1V, I <sub>C</sub> =50mA	60			
0-11-4	V <sub>CE(sat)</sub> *	Ic=10mA, I <sub>B</sub> =1mA			0.25	V
Collector-emitter saturation voltage		I <sub>C</sub> =50mA, I <sub>B</sub> =5mA			0.3	V
Door emitter estimation valtage	V <sub>BE(sat)</sub> *	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA			0.85	V
Base-emitter saturation voltage		lc=50mA, I <sub>B</sub> =5mA			0.95	V
Transition frequency	f⊤	V <sub>CE</sub> =20V,I <sub>C</sub> =10mA , f=100MHz	300			MHz
Collector output capacitance	Cob	V <sub>CB</sub> =5V, I <sub>E</sub> =0, f=1MHz			4	pF
Collector output capacitance	Cib	V <sub>EB</sub> =0.5V, I <sub>E</sub> =0, f=1MHz			8	рF
Delay time	t <sub>d</sub>	V <sub>CC</sub> =3V, V <sub>BE(off)</sub> =0.5V			35	ns
Rise time	tr	I <sub>C</sub> =10mA, I <sub>B1</sub> =1mA			35	ns
Storage time	ts	- \/ 3\/     - 10m A			225	ns
Fall time	t <sub>f</sub>	V <sub>CC</sub> =3V, I <sub>C</sub> =10mA, I <sub>B1</sub> = I <sub>B2</sub> =1mA			75	ns

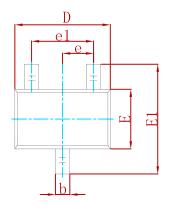
<sup>\*</sup>Pulse test: pulse width ≤300µs,duty cycle≤ 2.0%.

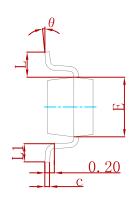


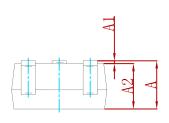




#### **PACKAGEMECHANICALDATA**

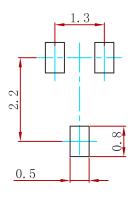






Symbol	Dimensions In Millimeters		Dimensions In Inches		
Syllibol	Min	Max	Min	Max	
Α	0.900	1.100	0.035	0.043	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.000	0.035	0.039	
b	0.200	0.400	0.008	0.016	
С	0.080	0.150	0.003	0.006	
D	2.000	2.200	0.079	0.087	
E	1.150	1.350	0.045	0.053	
E1	2.150	2.450	0.085	0.096	
е	0.650 TYP		0.026 TYP		
e1	1.200	1.400	0.047	0.055	
L	0.525 REF		0.021 REF		
L1	0.260	0.460	0.010	0.018	
θ	0°	8°	0°	8°	

## **Suggested Pad Layout**



#### Note:

- 1. Controlling dimension:in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.

### **REEL SPECIFICATION**

P/N	PKG	QTY
MMST3904	SOT-323	3000



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